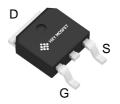


### **Description**

The FDD5690 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

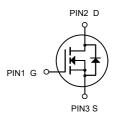


#### TO-252-2L

#### **General Features**

 $V_{DS} = 60V I_{D} = 30 A$ 

 $R_{DS(ON)}$  < 26m $\Omega$  @  $V_{GS}$ =10V



#### N-Channel MOSFET

## **Application**

**Battery protection** 

Load switch

Uninterruptible power supply

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
FDD5690	TO-252-2L	HXY MOSFET	2500

# Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter Rating		Units	
Vps	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	30	А	
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	15	А	
Ідм	Pulsed Drain Current <sup>2</sup>	46	А	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	25.5	mJ	
las	Avalanche Current	22.6	А	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	34.7	W	
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	2	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R <sub>θ</sub> JA	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W	
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	3.6	°C/W	



# Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	60			V
△BVDSS/△TJ	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.063		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =15A		22	26	
Rds(on)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A		30	38	mΩ
V <sub>G</sub> S(th)	Gate Threshold Voltage	V V 1 050 A	1.2		2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250uA$		-5.24		mV/°C
		V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
Igss	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =15A		17		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		3.2		Ω
Qg	Total Gate Charge (4.5V)			12.6		
Qgs	Gate-Source Charge	V <sub>DS</sub> =48V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =12A		3.2		nC
Q <sub>gd</sub>	Gate-Drain Charge			6.3		
Td(on)	Turn-On Delay Time			8		
Tr	Rise Time	V <sub>DD</sub> =30V , V <sub>GS</sub> =10V ,		14.2		
$T_{d(off)}$	Turn-Off Delay Time	_R <sub>G</sub> =3.3Ω, I <sub>D</sub> =10A		24.4		ns
T <sub>f</sub>	Fall Time			4.6		
C <sub>iss</sub>	Input Capacitance			1378		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		86		pF
Crss	Reverse Transfer Capacitance			64		
Is	Continuous Source Current <sup>1,5</sup>				23	Α
Іѕм	Pulsed Source Current <sup>2,5</sup>	−V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			46	Α
Vsp	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V

#### Note:

- 1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leqq 300 us$  , duty cycle  $\leqq 2\%$
- 3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=22.6A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.



#### **Typical Characteristics**

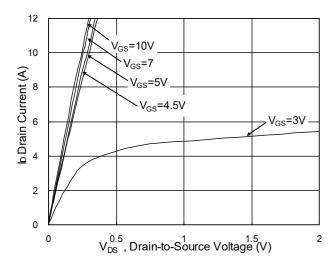


Fig.1 Typical Output Characteristics

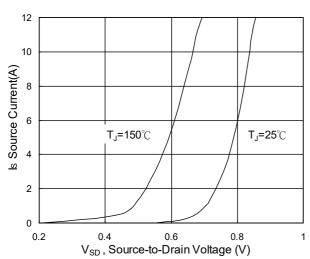


Fig.3 Forward Characteristics of Reverse

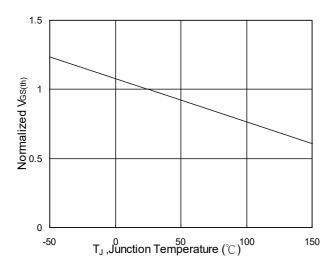


Fig.5 Normalized V<sub>GS(th)</sub> v.s T<sub>J</sub>

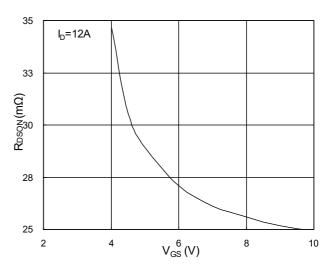


Fig.2 On-Resistance v.s Gate-Source

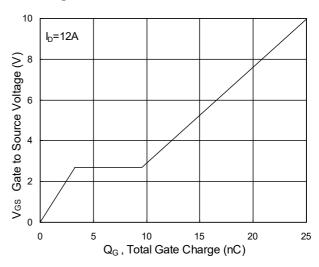


Fig.4 Gate-Charge Characteristics

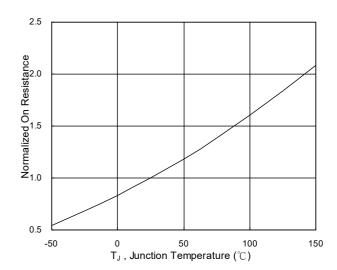
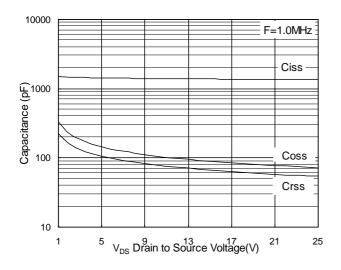


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>





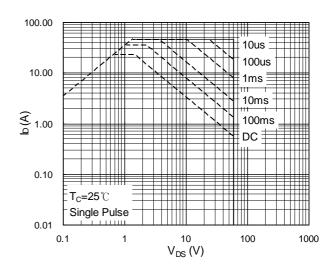


Fig.7 Capacitance

Fig.8 Safe Operating Area

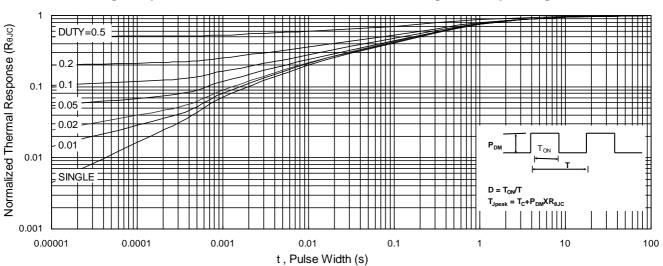


Fig.9 Normalized Maximum Transient Thermal Impedance

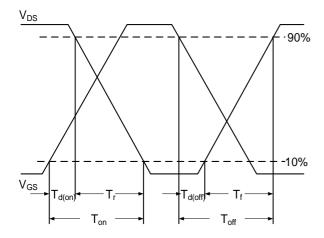


Fig.10 Switching Time Waveform

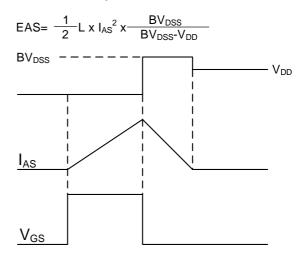
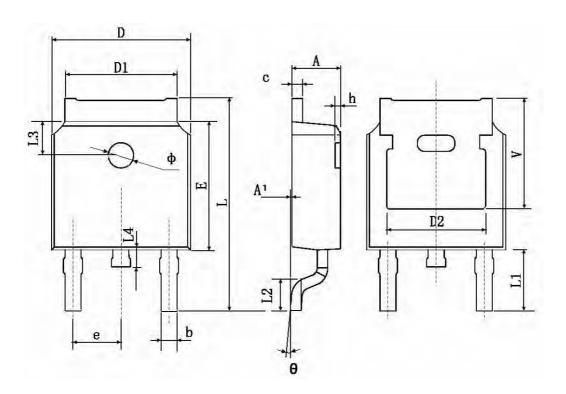


Fig.11 Unclamped Inductive Waveform



# **TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		

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